

MOSFET – Power, Dual N-Channel, for 1-Cell Lithium-ion Battery Protection

12 V, 3.2 mΩ, 27 A

EFC6611R

This Power MOSFET features a low on-state resistance. This device is suitable for applications such as power switches of portable machines. Best suited for 1-cell lithium-ion battery applications.

Features

- 2.5 V Drive
- 2 kV ESD HBM
- Common-Drain Type
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS Compliance

Applications

• 1-Cell Lithium-ion Battery Charging and Discharging Switch

SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Parameter	Symbol	Value	Unit
Source to Source Voltage	V _{SSS}	12	V
Gate to Source Voltage	V_{GSS}	±8	V
Source Current (DC)	I _S	27	Α
Source Current (Pulse) PW ≤ 100 μs, Duty Cycle ≤ 1%	I _{SP}	100	Α
Total Dissipation Surface mounted on ceramic substrate (5000 mm ² x 0.8 mm)	P _T	2.5	W
Junction Temperature	Tj	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

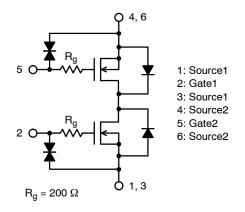
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient Surface mounted on ceramic substrate (5000 mm ² x 0.8 mm)	$R_{ hetaJA}$	50	°C/W

V _{SSS}	R _{SS(on)} MAX I _{S MA}	
12 V	$3.2~\mathrm{m}\Omega$ @ $4.5~\mathrm{V}$	27 A
	3.2 mΩ @ 4.0 V	
	3.2 mΩ @ 3.8 V	
	4.4 mΩ @ 3.1 V	
	6.3 mΩ @ 2.5 V	

ELECTRICAL CONNECTION N-Channel





CSP6, 1.77x3.54/ EFCP3517-6DGH-020 CASE 568AL

MARKING DIAGRAM

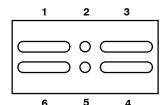
ML YMZZ

ML = Device CodeY = Year of Production

M = Month of Assembly Operation

ZZ = Assembly Lot Number

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Source to Source Breakdown Voltage	V(_{BR}) _{SSS}	I _S = 1 mA, V _{GS} = 0 V (Test Circuit 1)	12	-	-	V
Zero-Gate Voltage Source Current	I _{SSS}	V _{SS} = 10 V, V _{GS} = 0 V (Test Circuit 1)	-	-	1	μΑ
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±8 V, V _{SS} = 0 V (Test Circuit 2)	-	-	±1	μΑ
Gate Threshold Voltage	V _{GS} (th)	V _{SS} = 6 V, I _S = 1 mA (Test Circuit 3)	0.5	-	1.3	V
Forward Transconductance	9 _{FS}	V _{SS} = 6 V, I _S = 3 A (Test Circuit 4)	-	19	-	S
Static Source to Source On-State Resistance	R _{SS(on)} 1	I _S = 5 A, V _{GS} = 4.5 V (Test Circuit 5)	1.8	2.3	3.2	mΩ
	R _{SS(on)} 2	I _S = 5 A, V _{GS} = 4.0 V (Test Circuit 5)	1.9	2.4	3.2	mΩ
	R _{SS(on)} 3	I _S = 5 A, V _{GS} = 3.8 V (Test Circuit 5)	2.0	2.6	3.2	mΩ
	R _{SS(on)} 4	I _S = 5 A, V _{GS} = 3.1 V (Test Circuit 5)	2.1	3.3	4.4	mΩ
	R _{SS(on)} 5	I _S = 5 A, V _{GS} = 2.5 V (Test Circuit 5)	2.7	4.0	6.3	mΩ
Turn-ON Delay Time	t _{d(on)}	V _{SS} = 6 V, V _{GS} = 4.5 V, I _S = 3 A	-	80	-	ns
Rise Time	t _r	- (Test Circuit 6)	-	570	=	ns
Turn-OFF Delay Time	t _{d(off)}	1	-	38,000	=	ns
Fall Time	t _f	1	-	17,700	=	ns
Total Gate Charge	Qg	V_{SS} = 6 V, V_{GS} = 4.5 V, I_{S} = 27 A (Test Circuit 7)	-	100	-	nC
Forward Source to Source Voltage	$V_{F(S-S)}$	I _S = 3 A, V _{GS} = 0 V (Test Circuit 8)	_	0.75	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing) [†]
EFC6611R-TF	ML	CSP6, 1.77 × 3.54 EFCP3517-6DGH-020 (Pb–Free / Halogen Free)	5,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TEST CIRCUITS ARE EXAMPLE OF MEASURING FET1 SIDE

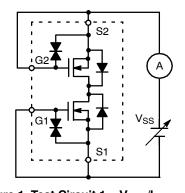
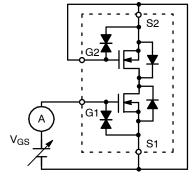


Figure 1. Test Circuit 1 – V_{SSS}/I_{SSS}



When FET1 is measured, Gate and Source of FET2 are short-circuited.

Figure 2. Test Circuit 2 - I_{GSS}

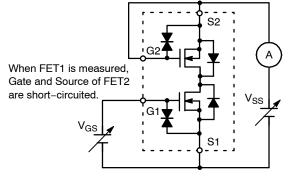
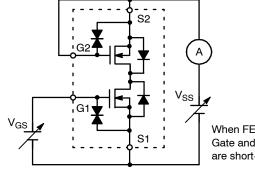


Figure 3. Test Circuit 3 - V_{GS}(th)



When FET1 is measured, Gate and Source of FET2 are short-circuited.

Figure 4. Test Circuit 4 - g_{FS}

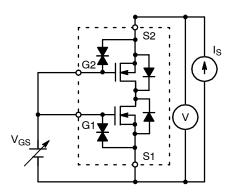


Figure 5. Test Circuit 5 - R_{SS(on)}

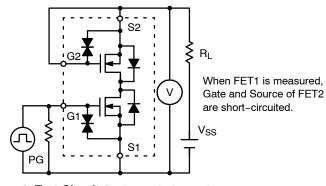


Figure 6. Test Circuit 6 – $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

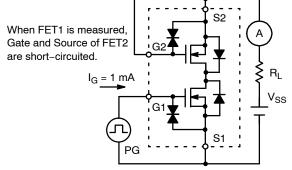


Figure 7. Test Circuit 7 - Qq

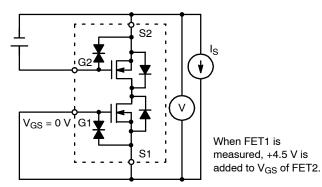
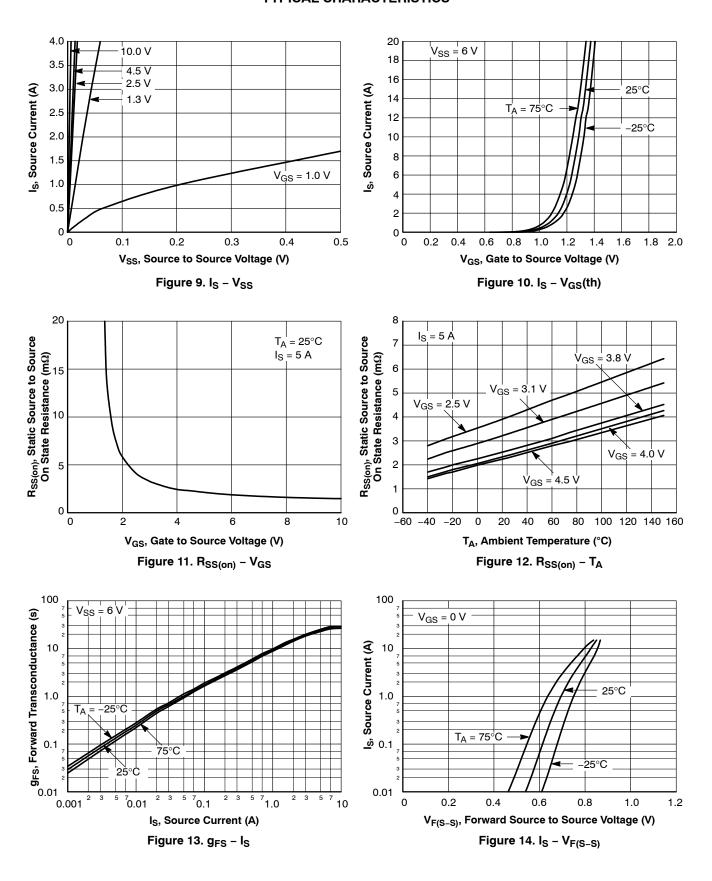


Figure 8. Test Circuit 8 - V_{F(S-S)}

NOTE: When FET2 is measured, the position of FET1 and FET2 is switched.

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS (Continued)

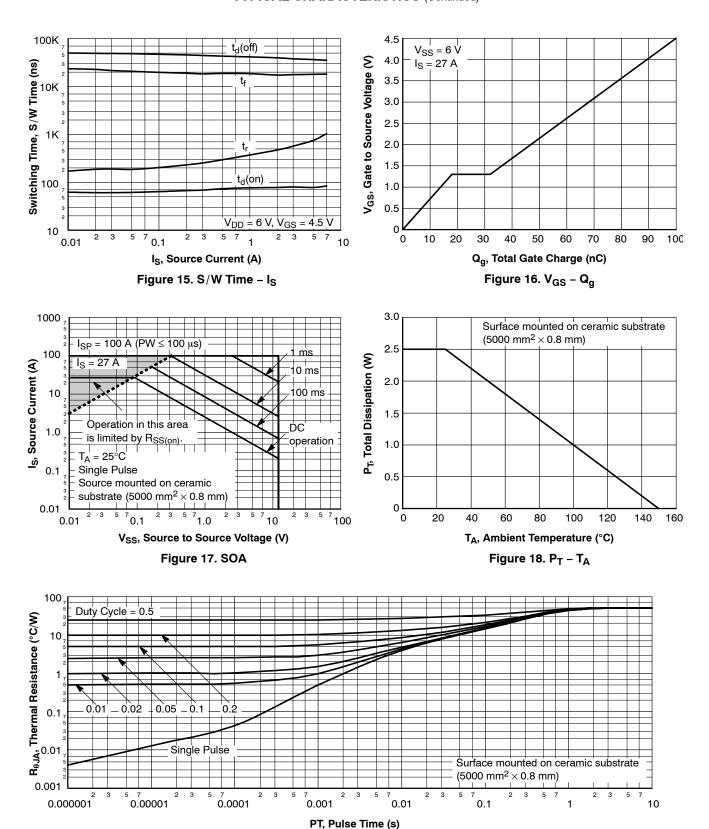


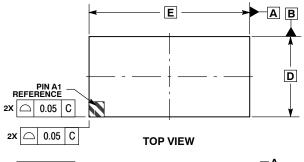
Figure 19. $R_{\theta JA}$ – Pulse Time



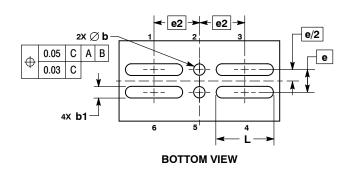


CSP6, 1.77x3.54 / EFCP3517-6DGH-020 CASE 568AL ISSUE O

DATE 23 OCT 2013





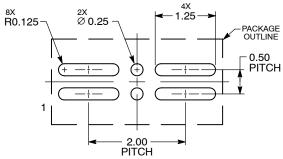


NOTES:

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS.

	MILLIMETERS		
DIM	MIN MAX		
Α		0.22	
b	0.22	0.28	
b1	0.22	0.28	
D	1.77 BSC		
E	3.54 BSC		
е	0.50 BSC		
e2	1.00 BSC		
L	1.22	1.28	

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON79069F	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	CSP6, 1.77X3.54 / EFCP3517-6DGH-020		PAGE 1 OF 1

onsemi and ONSeMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

onsemi:

EFC6611R-A-TF